

**DECLARATION (37 CFR 1.63) FOR UTILITY OR DESIGN APPLICATION USING AN
APPLICATION DATA SHEET (37 CFR 1.76)**

Electronic Version v11

Stylesheet Version v10

**Title of
Invention**

METHOD OF INTEGRATING HIGH VOLTAGE METAL OXIDE
SEMICONDUCTOR DEVICES AND SUBMICRON METAL OXIDE
SEMICONDUCTOR DEVICES

As the below named inventors, we declare that:

This declaration is directed to the invention titled: " METHOD OF INTEGRATING HIGH VOLTAGE METAL OXIDE SEMICONDUCTOR DEVICES AND SUBMICRON METAL OXIDE SEMICONDUCTOR DEVICES"

We believe that we are the original and first inventors of the subject matter which is claimed and for which a patent is sought;

We have reviewed and understand the contents of the above-identified application, including the claims, as amended by any amendment specifically referred to above;

We acknowledge the duty to disclose to the United States Patent and Trademark Office all information known to us to be material to patentability as defined in 37 CFR 1.56, including for continuation-in-part applications, material information which became available between the filing date of the prior application and the national or PCT International filing date of the continuation-in-part application.

All statements made herein of own knowledge are true, all statements made herein on information and belief are believed to be true, and further that these statements were made with the knowledge that willful false statements and the like are punishable by fine or imprisonment, or both, under 18 U.S.C. 1001, and may jeopardize the validity of the application or any patent issuing thereon.

FULL NAME OF INVENTORS:

Inventor 1: Ching-Chun Huang	Inventor
Signature :	Citizen of : TW
Inventor 2: Ming-Hsien Huang	Inventor
Signature :	Citizen of : TW

Inventor 3: Rong-Ching Chen	Inventor
Signature :	Citizen of : TW
Inventor 4: Jy-Hwang Lin	Inventor
Signature :	Citizen of : TW

COMBINED DECLARATION AND POWER OF ATTORNEY

As a below named inventor , I hereby declare that :

I believe I am the sole (if only one name appears below) , or joint (if more than one name appears) , original and first inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled :

"METHOD OF INTEGRATING HIGH VOLTAGE METAL OXIDE SEMICONDUCTOR DEVICES AND SUBMICRON METAL OXIDE SEMICONDUCTOR DEVICES"

+ The specification for the above entitled invention is filed herewith.

_____ The specification for the above entitled invention was filed previously
with application serial number: _____ Filing Date: _____

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to the patentability of the invention disclosed in this application in accordance with Title 37, Code of Federal Regulations, Section 1.56 (a). I further acknowledge the duty in any continuation-in-part application to disclose to the Patent and Trademark Office all information known to be material to the patentability of the invention disclosed in this application, as defined in 1.56, which became available to me between the filing date of the prior application and the filing date of this application.

PRIORITY CLAIM

There is no claim of priority

Claim of priority is based on the following:

POWER OF ATTORNEY

As a named inventor, I hereby appoint the following attorneys to prosecute this application and to transact all related business in the Patent and Trademark Office:

Winston Hsu

Registration# 41,526

P.O. Box 506,
Merrifield, Virginia 22116,
U.S.A

E-mail : winstonhsu@naipo.com.tw

TEL: +886-2-89237350 *100

DECLARATION

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment or both under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued hereon.

Date: 11/20/2003 Ching-chun Huang
Printed Name: Ching-Chun Huang
Post Office Address: 1B, 11F, No. 169-10, Sec. 3, Hsi-Tun Rd., Tai-chun
and Residence City, R.O.C, Tai-Chung City, Taiwan, R.O.C.
Citizen of: R.O.C.

Date: 11/20/2003 Ming-Hsien Huang
Printed Name: Ming-Hsien Huang
Post Office Address: 2F, No. 2, Lane 36, Hsing-Chung St., Hsin-Chu City,
and Residence Taiwan, R.O.C.
Citizen of: R.O.C.

Date: 11/24/2003 Rong-ching Chen
Printed Name: Rong-Ching Chen
Post Office Address: No. 10, Lane 35, Sec. 3, Sa-Tien Rd., Ta-Tu Hsiang,
and Residence Tai-Chung City, Taiwan, R.O.C.
Citizen of: R.O.C.

Date: 11/24/2003 Jy-hwg Lin
Printed Name: Jy-Hwang Lin
Post Office Address: 18F-2, No. 13, Lane 175, Wu-Ling Rd., Hsin-Chu City,
and Residence Taiwan, R.O.C.
Citizen of: R.O.C.